

SBR40U150CT - Prel SBR40U150CTF - Prel SBR40U150CTI - Prel SBR40U150CTB - Prel

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I _{F(AV)} Rectangular Waveform	40	Α
V_{RRM}	150	V
V _F @20A, Tj=125 ^O C	0.73	V, typ
Tj (operating/storage)	-65 to 175	°C

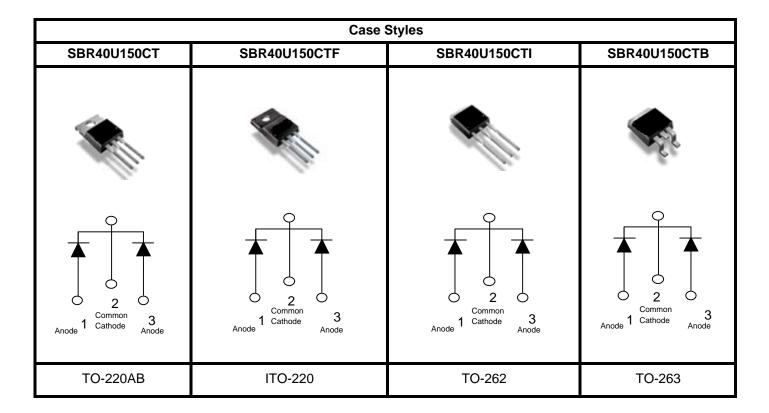
Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

ELECTRICAL:

- * Ultra-Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 175°C Operating Junction Temperature

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages



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Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified) SYMBOL **UNITS** DC Blocking Voltage V_{RM} Working Peak Reverse Voltage 150 Volts V_{RWM} Peak Repetitive Reverse Voltage V_{RRM} Average Rectified Forward Current (Rated V_R-20Khz Square Wave) - 50% duty 40 I_{\circ} **Amps** Peak Forward Surge Current - 1/2 60hz \mathbf{I}_{FSM} 300 **Amps** Peak Repetitive Reverse Surge Current 3 **Amps** I_{RRM} (2uS-1Khz) Instantaneous Forward Voltage (per leg) Max Typ $I_{\rm F} = 20A; T_{\rm I} = 25^{\circ}C$ ٧ 0.80 Volts $I_F = 20A; T_J = 125^{\circ}C$ 0.76 Maximum Instantaneous Reverse Current at Max Typ Rated V_{RM} 0.5 I_R mΑ $T_1 = 25^{\circ}C$ 25 mΑ $T_{J} = 125^{\circ}C$ Maximum Rate of Voltage Change dv/dt 10,000 V/uS (at Rated V_R)

Package = ITO-220

Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263

Operating and Storage Junction Temperature

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 $R\theta_{JC}$

 $T_{\rm J}$

APD Semiconductor, Inc.

1 Lagoon Drive, Suite 410, Redwood City, CA 94065, USA Ph: 650 508 8896 FAX: 650 508 8865 Homepage: www.apdsemi.com email: info@apdsemi.com

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-65 to +175

°C/W

οС

^{*} Pulse width < 300 uS, Duty cycle < 2%